

NPN SILICON RF TRANSISTOR

DESCRIPTION:

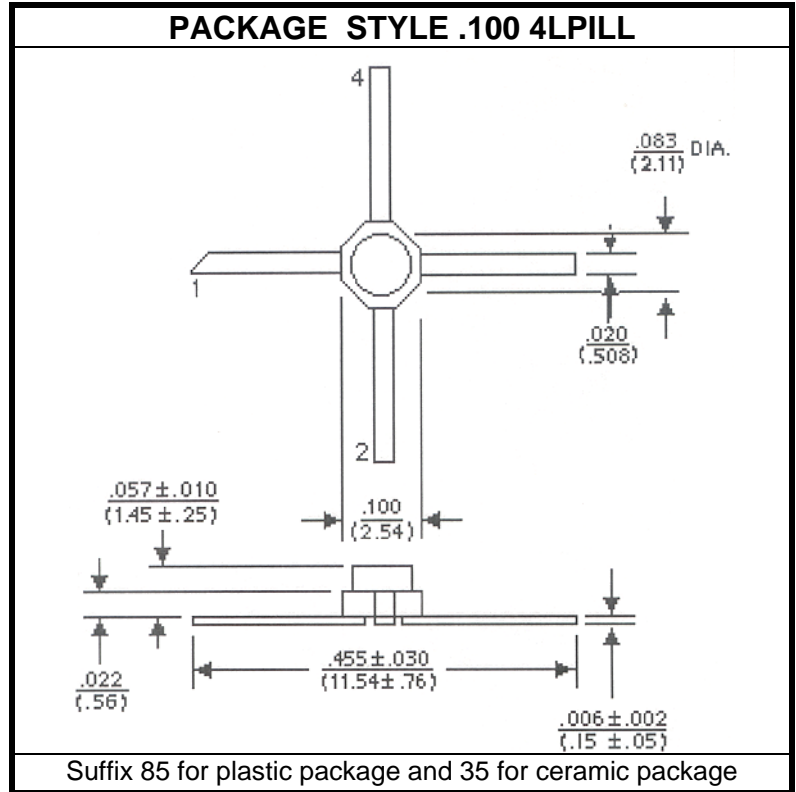
The **ASI NE02135** is Designed for Oscillator and Amplifier Applications up to 2.0 GHz.

FEATURES INCLUDE:

- High insertion gain.
- High power gain.
- Low Noise figure

MAXIMUM RATINGS

I_C	70 mA
V_{CB0}	25 V
V_{CEO}	12 V
V_{EBO}	3.0 V
P_{DISS}	3.3 W @ T _A = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	53 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CB0}	V _{CB} = 15 V					1.0	μA
I_{EBO}	V _{EB} = 2.0 V					1.0	μA
h_{FE}	V _{CE} = 10 V	I _C = 20 mA		20		250	---
C_{CB}	V _{CB} = 10 V		f = 1.0 MHz		0.6	1.0	pF
f_t	V _{CE} = 10 V	I _C = 20 mA	f = 1.0 GHz		4.5		GHz
 S₂₁ ²	V _{CE} = 10 V	I _C = 20 mA	f = 0.5 GHz		18.5		dB
			f = 1.0 GHz		13		
			f = 2.0 GHz	5.0	5.7		
NF_{MIN}	V _{CE} = 10 V	I _C = 3.0 mA	f = 0.5 GHz		1.5	4.0	dB
	V _{CE} = 10 V	I _C = 5.0 mA	f = 2.0 GHz		2.7		
MAG	V _{CE} = 10 V	I _C = 20 mA	f = 0.5 GHz		22		dB
			f = 1.0 GHz		18		
			f = 2.0 GHz		11		